

N-Channel Enhancement Mode Power MOSFET

MTN3410F3

BV_{DSS} : 100V
$R_{DS(ON)}$: 20mΩ (max.)
I_D : 59A

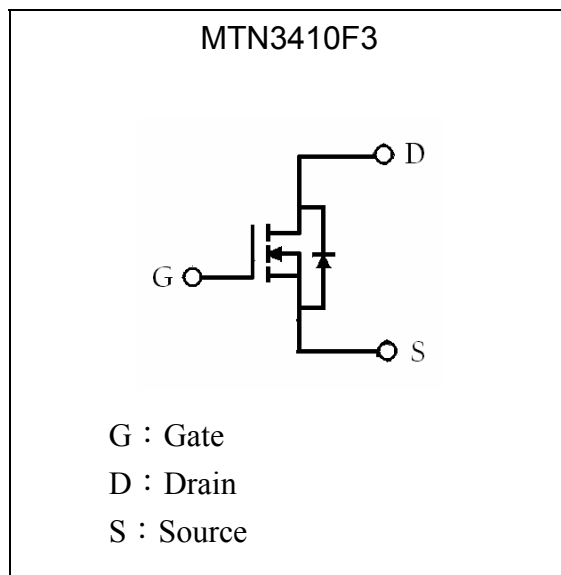
Description

The MTN3410F3 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-263 package is universally preferred for all commercial-industrial applications

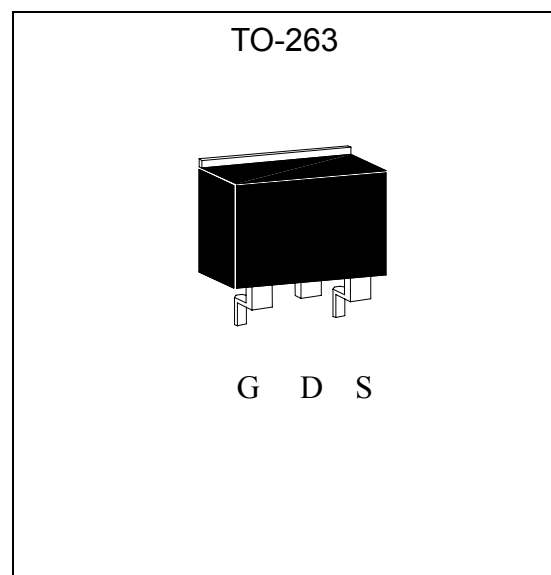
Features

- $BV_{DSS}=100V$
- Low On Resistance
- Simple Drive Requirement
- Fast Switching Characteristic
- RoHS compliant package

Symbol



Outline



**Absolute Maximum Ratings** ($T_C=25^{\circ}\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	59*	A
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$	I_D	40*	A
Pulsed Drain Current @ $V_{GS}=10\text{V}$ (Note 1)	I_{DM}	236*	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	132	mJ
Avalanche Current (Note 1)	I_{AR}	59	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	11	mJ
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Total Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	110	W
Linear Derating Factor		0.88	W/ $^{\circ}\text{C}$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^{\circ}\text{C}$

*Drain current limited by maximum junction temperature

Note : 1.Repetitive rating; pulse width limited by maximum junction temperature.

2. $I_{AS}=59\text{A}$, $V_{DD}=50\text{V}$, $L=76\mu\text{H}$, $R_G=25\Omega$, starting $T_j=+25^{\circ}\text{C}$.

3. $I_{SD}\leq 59\text{A}$, $dI/dt\leq 100\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, starting $T_j=+25^{\circ}\text{C}$.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1.13	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max*	$R_{th,j-a}$	40	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5	$^{\circ}\text{C}/\text{W}$

*When mounted on the minimum pad size (PCB mount).



Characteristics (Tj=25°C, unless otherwise specified)

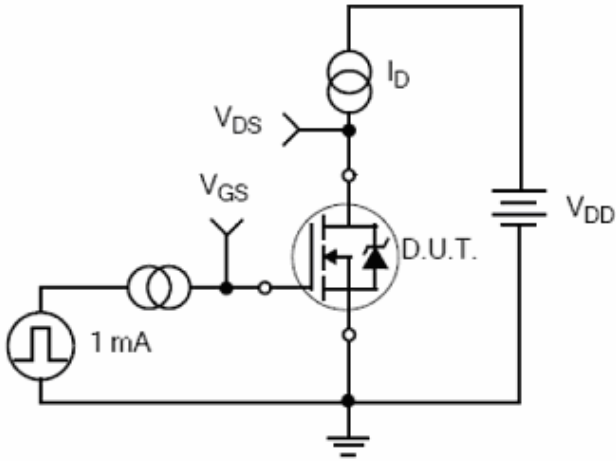
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	100	-	-	V	V _{GS} =0, I _D =250μA, T _j =25°C
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	25	-	S	V _{DS} =15V, I _D =29.5A
I _{GSS}	-	-	±100	nA	V _{GS} =±20
I _{DSS}	-	-	1	μA	V _{DS} =100V, V _{GS} =0
	-	-	10		V _{DS} =80V, V _{GS} =0, T _j =125°C
*R _{DS(ON)}	-	-	20	mΩ	V _{GS} =10V, I _D =29.5A
Dynamic					
*Q _g	-	-	75	nC	V _{DS} =80V, I _D =59A, V _{GS} =10V
*Q _{gs}	-	-	25		
*Q _{gd}	-	-	20		
*t _{d(ON)}	-	-	104	ns	V _{DS} =50V, I _D =59A, V _{GS} =10V, R _G =25Ω
*t _r	-	-	338		
*t _{d(OFF)}	-	-	182		
*t _f	-	-	176		
C _{iss}	-	-	4760	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	-	450		
C _{rss}	-	-	210		
Source-Drain Diode					
*I _S	-	-	59	A	
*I _{SM}	-	-	236		
*V _{SD}	-	-	1.5	V	I _S =59A, V _{GS} =0V
*t _{rr}	-	-	110	ns	V _{GS} =0, I _F =59A, dI/dt=100A/μs
*Q _{rr}	-	-	320	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

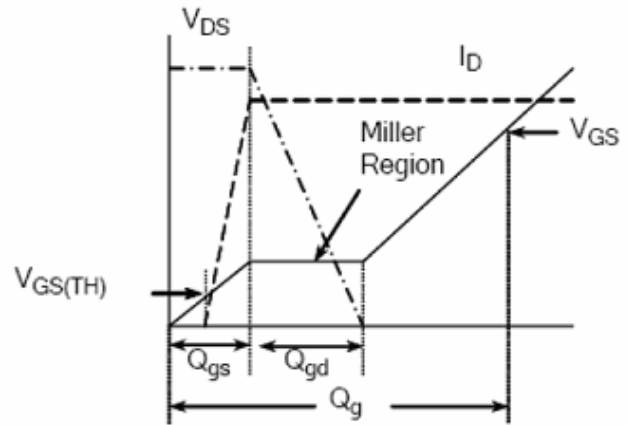
Ordering Information

Device	Package	Shipping
MTN3410F3	TO-263 (RoHS compliant)	800 pcs/ Tape & Reel

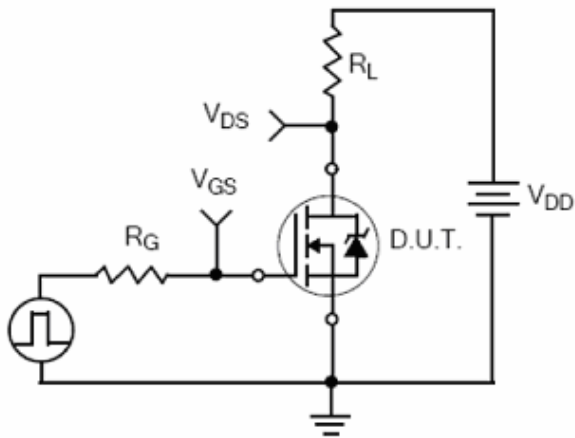
Test Circuit and Waveforms



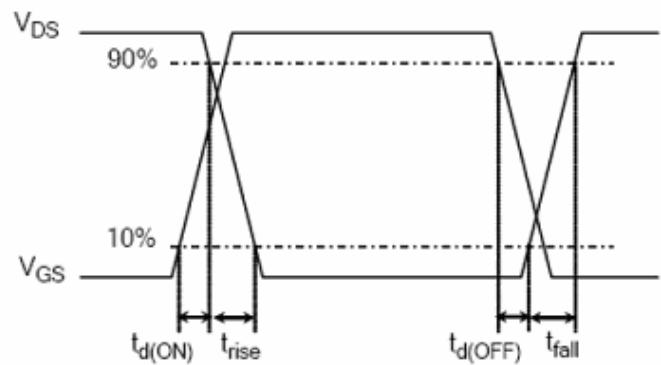
Gate Charge Test Circuit



Gate Charge Waveform

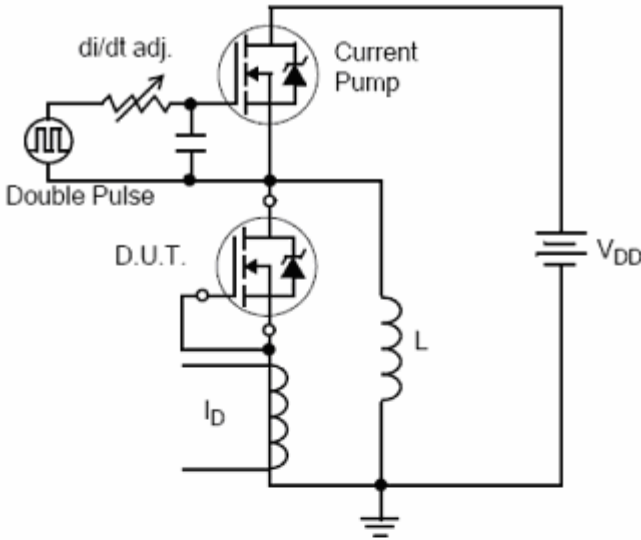


Resistive Switching Test Circuit

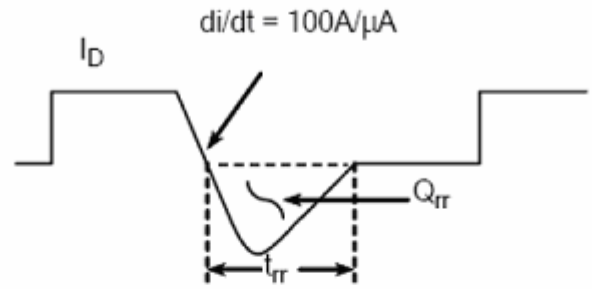


Resistive Switching Waveforms

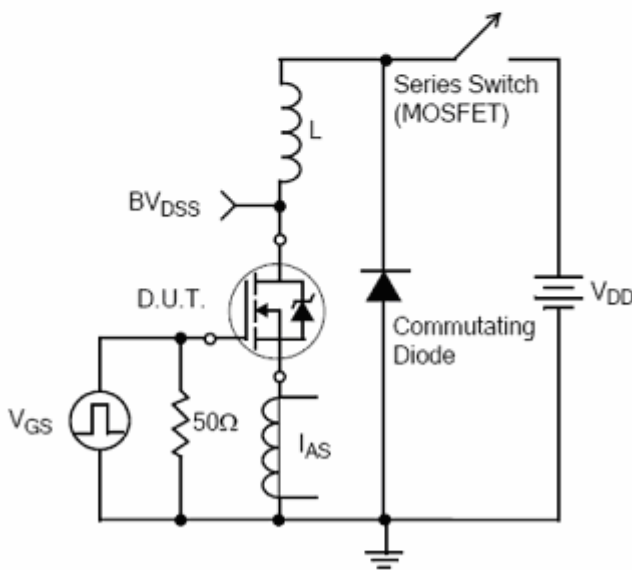
Test Circuit and Waveforms(Cont.)



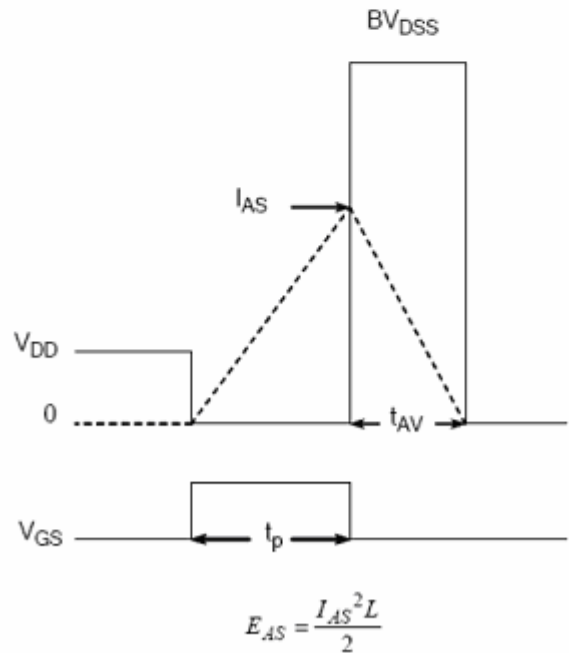
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform

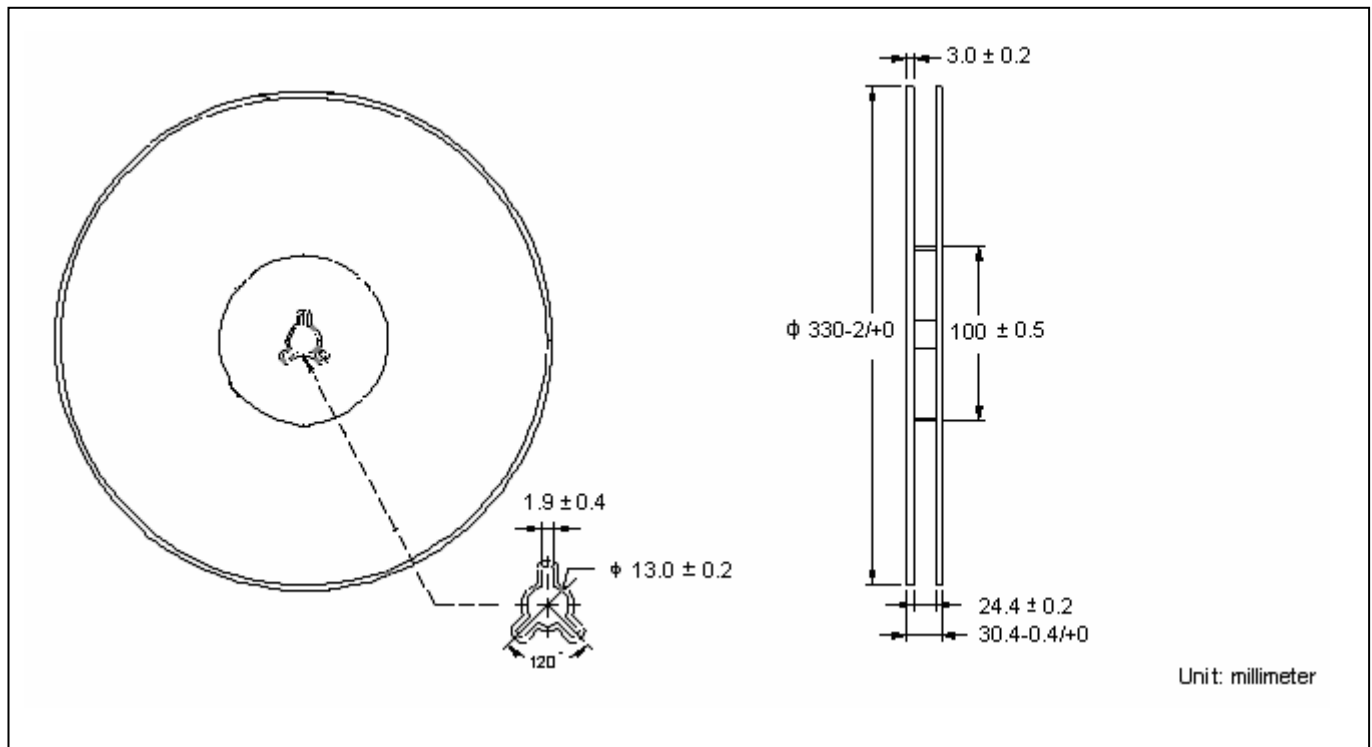


Unclamped Inductive Switching Test Circuit

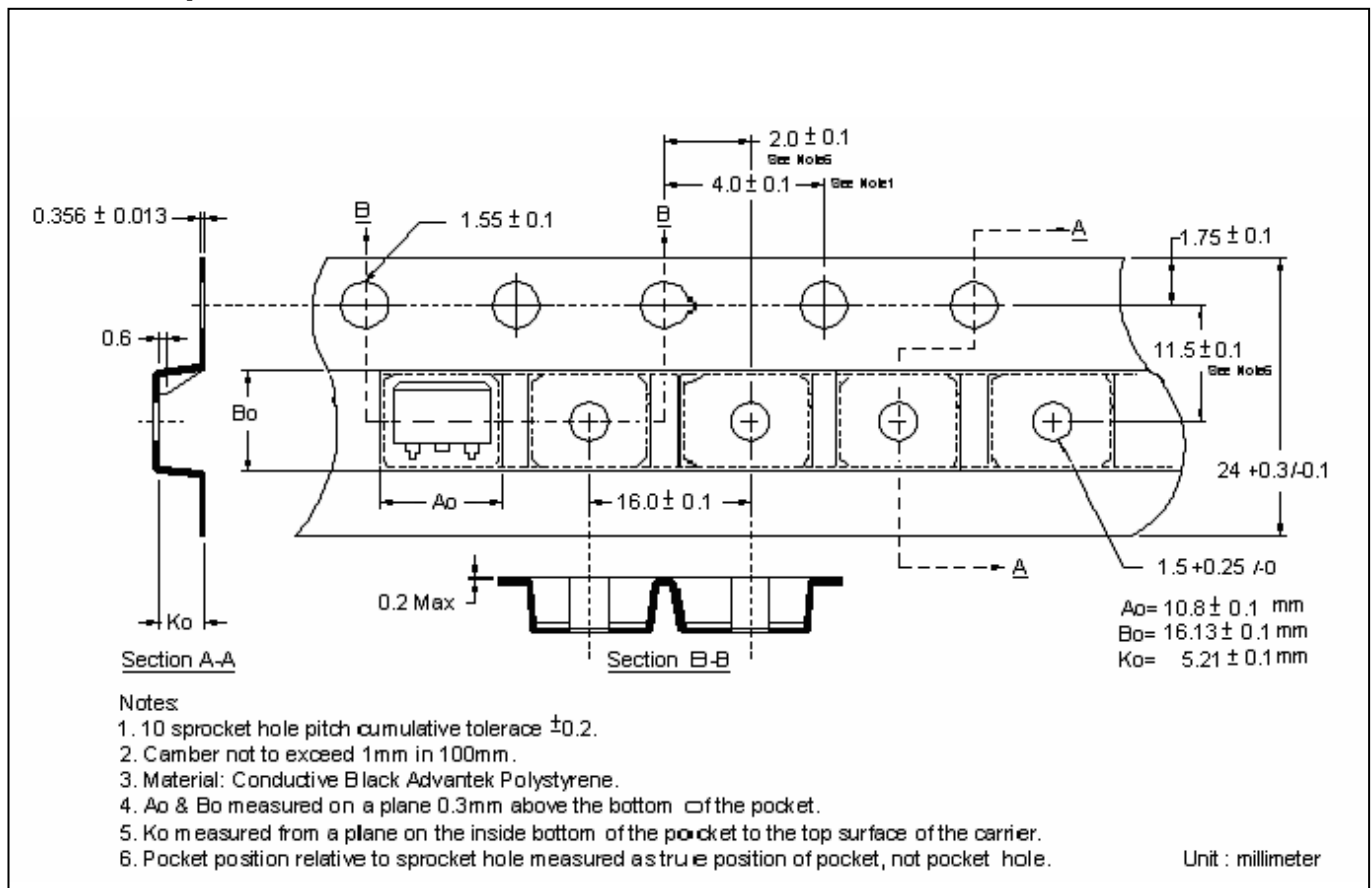


Unclamped Inductive Switching Waveforms

Reel Dimension



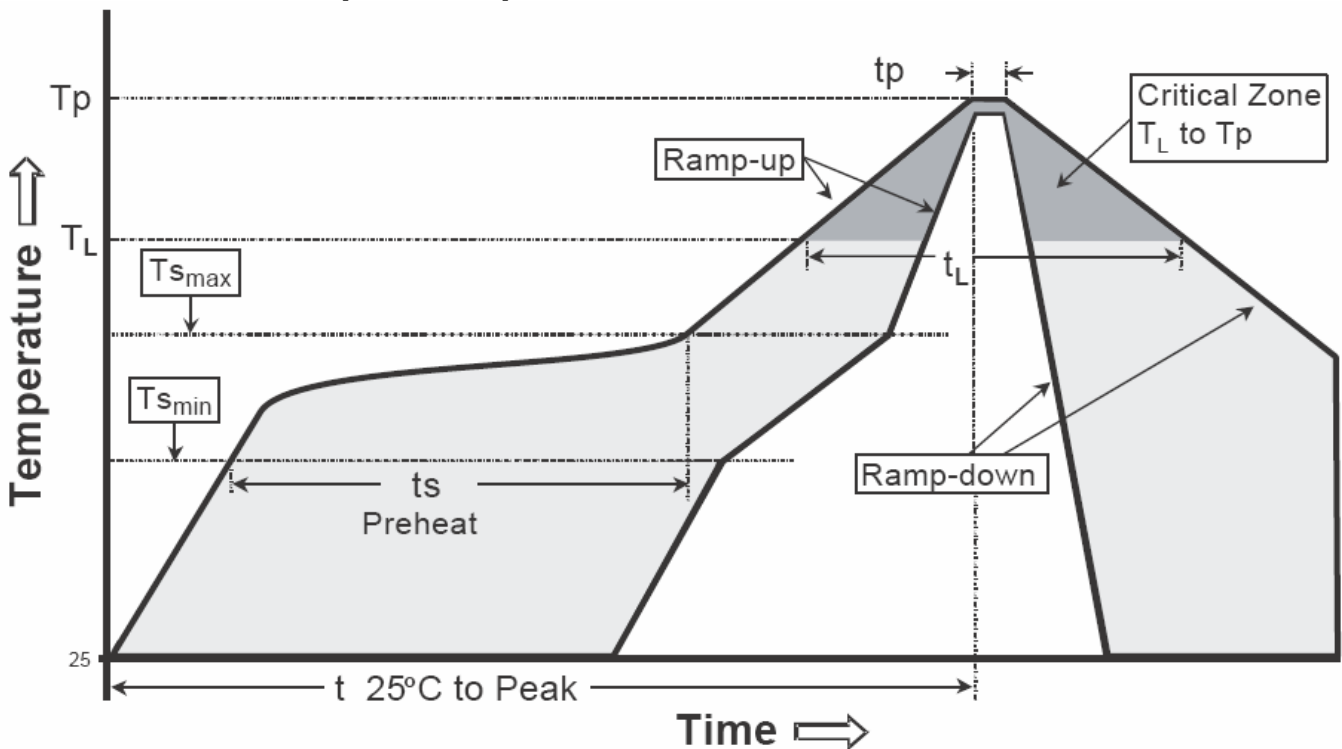
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

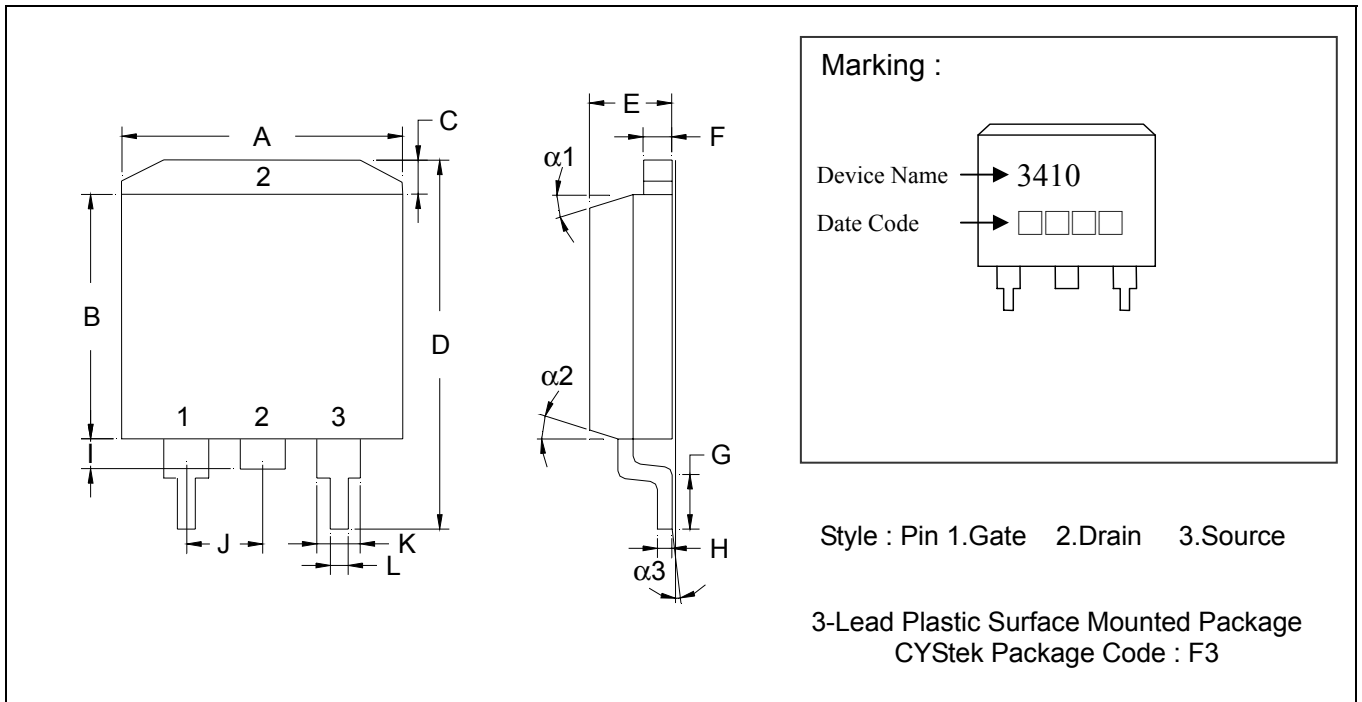
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-263 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.3800	0.4050	9.65	10.29	I	0.0500	0.0700	1.27	1.78
B	0.3300	0.3700	8.38	9.40	J	-	*0.1000	-	*2.54
C	-	0.0550	-	1.40	K	0.0450	0.0550	1.14	1.40
D	0.5750	0.6250	14.61	15.88	L	0.0200	0.0390	0.51	0.99
E	0.1600	0.1900	4.06	4.83	$\alpha 1$	-	-	6°	8°
F	0.0450	0.0550	1.14	1.40	$\alpha 2$	-	-	6°	8°
G	0.0900	0.1100	2.29	2.79	$\alpha 3$	-	-	0°	5°
H	0.0180	0.0290	0.46	0.74					

Notes : 1.Controlling dimension : millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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